
2SJ174

Silicon P-Channel MOS FET

HITACHI

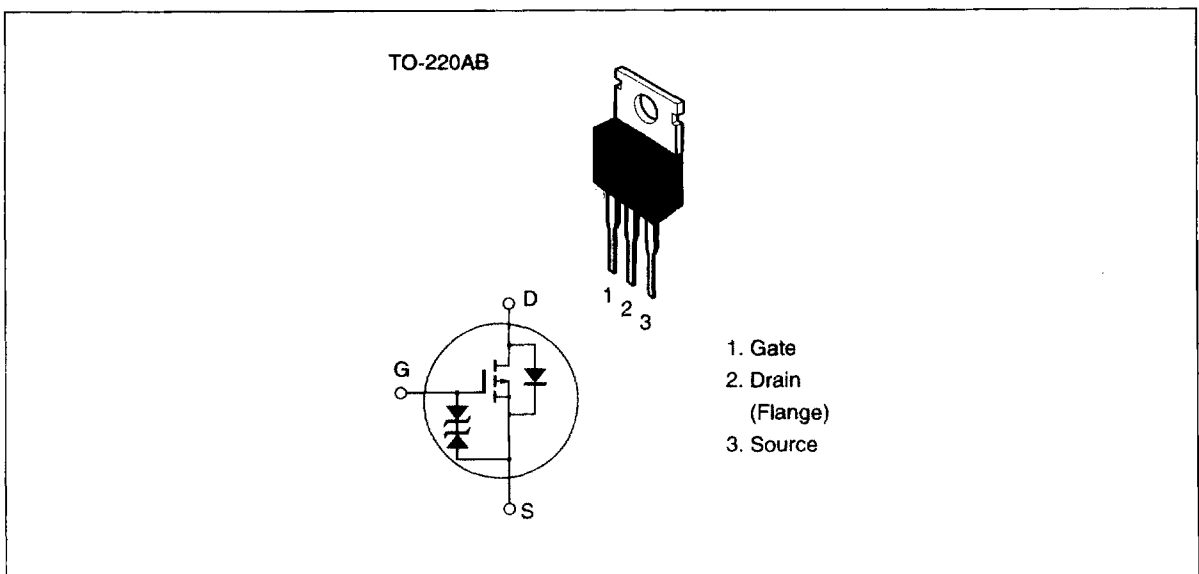
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	-60	V
Gate to source voltage	V_{GS}	±20	V
Drain current	I_D	-20	A
Drain peak current	$I_{D(pulse)}^{*1}$	-80	A
Body to drain diode reverse drain current	I_{DR}	-20	A
Channel dissipation	P_{ch}^{*2}	75	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

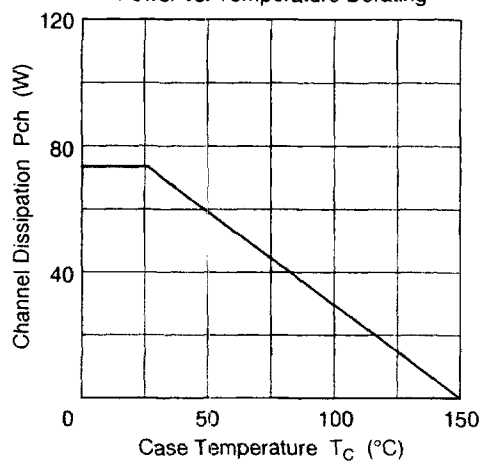
2. Value at $T_C = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

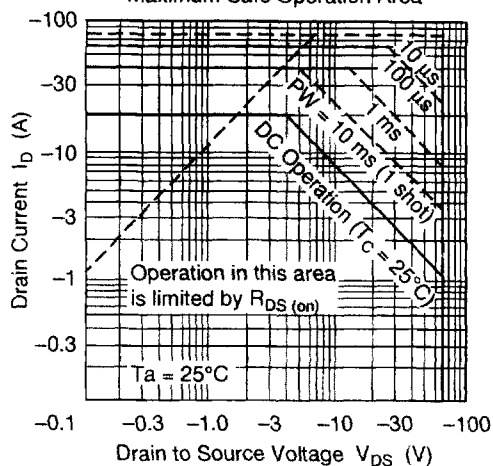
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DS}$	-60	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-250	μA	$V_{DS} = -50 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.065	0.085	Ω	$I_D = -10 \text{ A}$, $V_{GS} = -10 \text{ V}^{*1}$
		—	0.09	0.13		$I_D = -10 \text{ A}$, $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	8	13	—	S	$I_D = -10 \text{ A}$, $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	1850	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$,
Output capacitance	C_{oss}	—	990	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	265	—	pF	
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = -10 \text{ A}$, $V_{GS} = -10 \text{ V}$,
Rise time	t_r	—	125	—	ns	$R_L = 3 \Omega$
Turn-off delay time	$t_{d(off)}$	—	345	—	ns	
Fall time	t_f	—	235	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.2	—	V	$I_F = -20 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	230	—	ns	$I_F = -20 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu s$

Note: 1. Pulse test

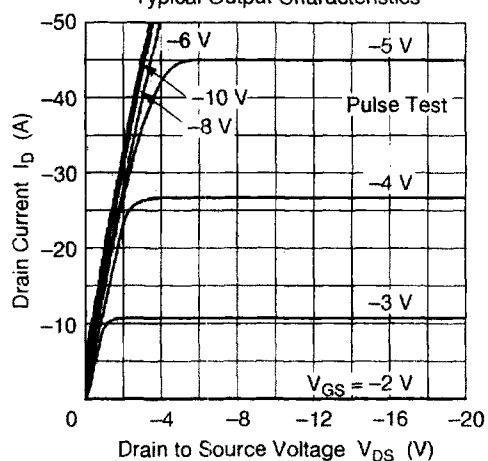
Power vs. Temperature Derating



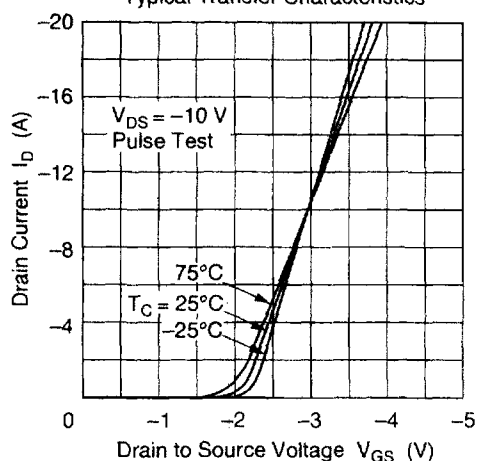
Maximum Safe Operation Area

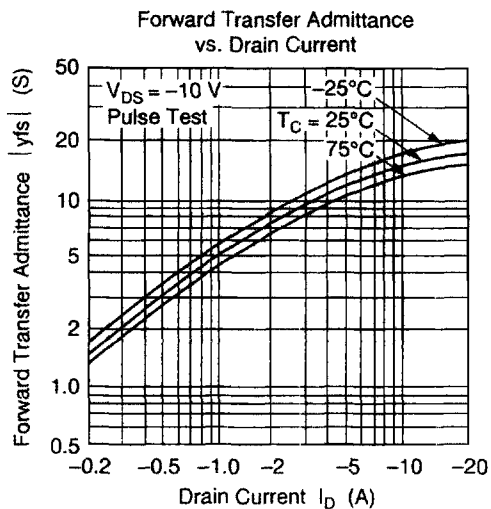
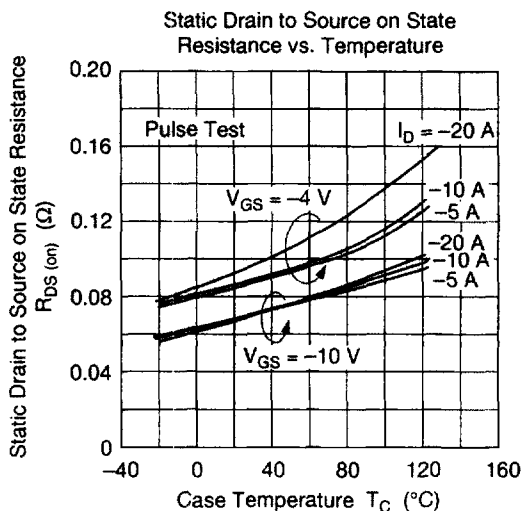
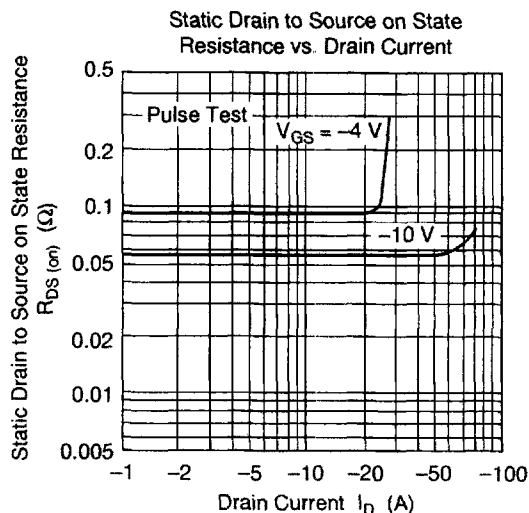
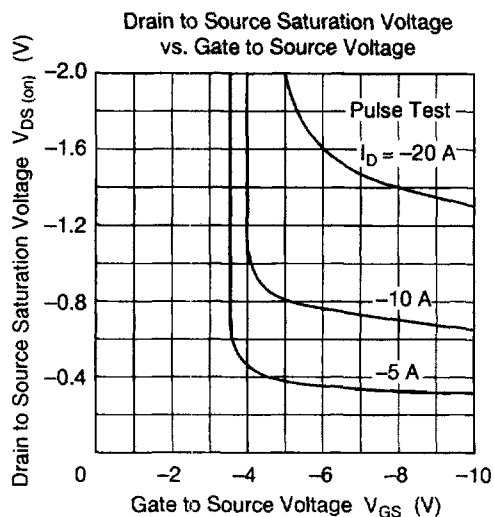


Typical Output Characteristics

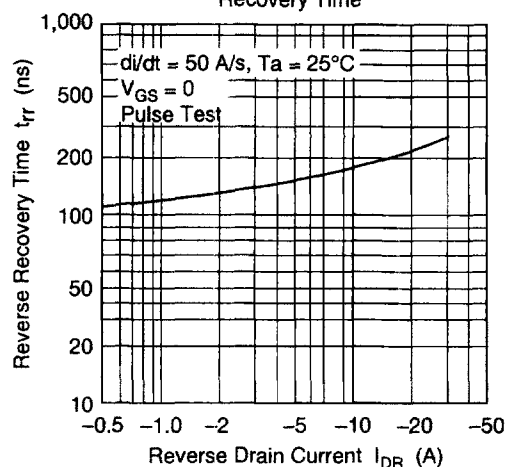


Typical Transfer Characteristics

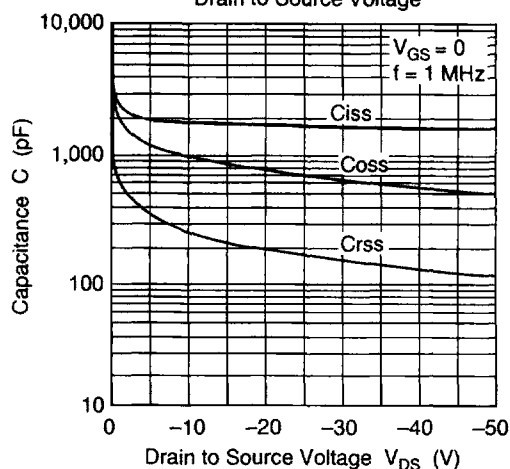




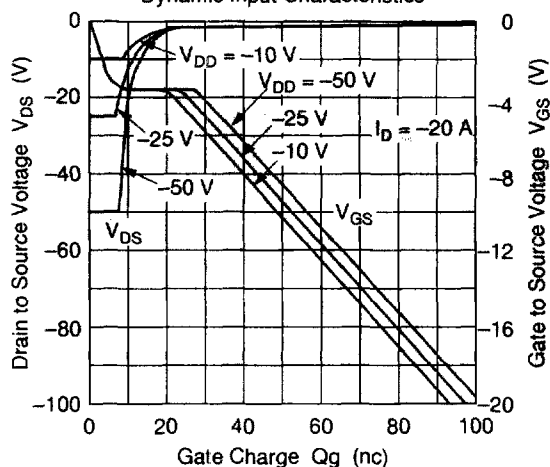
Body to Drain Diode Reverse Recovery Time



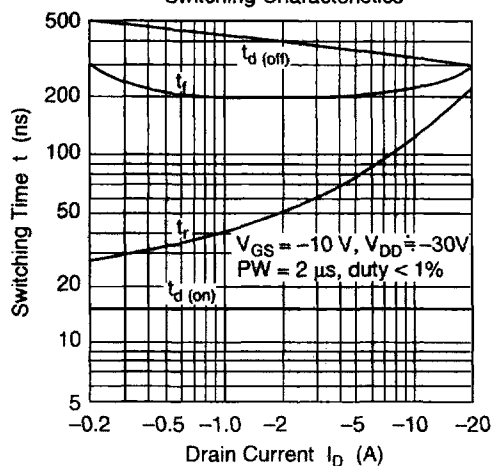
Typical Capacitance vs. Drain to Source Voltage

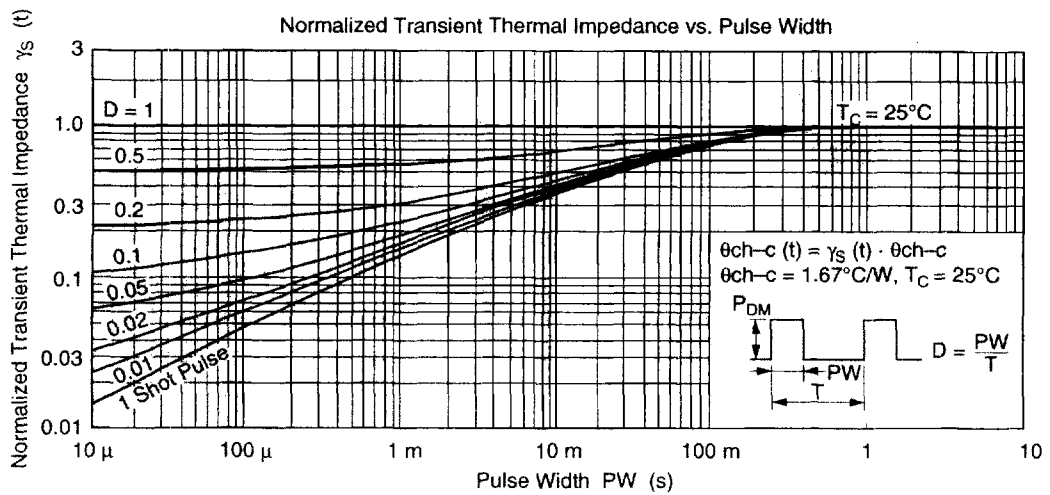
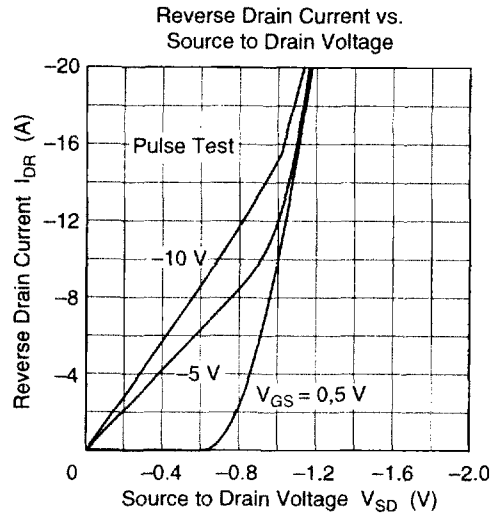


Dynamic Input Characteristics

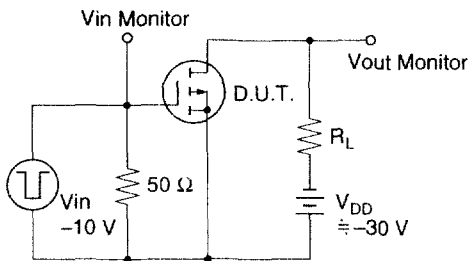


Switching Characteristics





Switching Time Test Circuit



Waveforms

